

Sixpack

SKiiP 39AC12T4V21

Features*

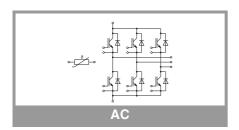
- Trench 4 IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised: File no. E63532
- Insulated by Si3N4 (Silicon Nitride) AMB (Active Metal Brazed) ceramic substrate for optimized thermal performance

Typical Applications

- Inverter up to 50 kVA
- Typical motor power 30 kW

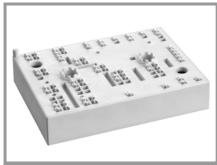
Remarks

- Max. case temperature limited to T_C=125°C
- Product reliability results valid for $T_j \le 150^{\circ}\text{C}$ (recommended $T_{j,\text{op}} = -40... + 150^{\circ}\text{C}$)
- For short circuit: Soft R_{Goff} recommended
- MiniSKiiP "Technical Explanations" and "Mounting Instructions" are part of the data sheet. Please refer to both documents for further information.



Absolute	Maximum Ratings	3		
	Conditions		Values	Unit
Inverter - I	I IGBT			
V _{CES}	T _j = 25 °C		1200	V
Ic	λ _{paste} =0.8 W/(mK)	T _s = 25 °C	189	Α
	T _j = 175 °C	T _s = 70 °C	154	Α
Ic	λ _{paste} =2.5 W/(mK)	T _s = 25 °C	249	Α
	T _j = 175 °C	T _s = 70 °C	204	Α
I _{Cnom}			150	Α
I _{CRM}			450	Α
V _{GES}			-20 20	V
t _{psc}	$V_{CC} = 800 \text{ V}$ $V_{GE} \le 15 \text{ V}$ $V_{CES} \le 1200 \text{ V}$	T _j = 150 °C	10	μs
Tj			-40 175	°C
Inverse - E	Diode			
V_{RRM}	T _j = 25 °C		1200	V
I _F	λ _{paste} =0.8 W/(mK)	T _s = 25 °C	149	Α
	T _j = 175 °C	T _s = 70 °C	118	Α
I _F	λ _{paste} =2.5 W/(mK)	T _s = 25 °C	221	Α
	T _j = 175 °C	T _s = 70 °C	177	Α
I _{FRM}			450	Α
I _{FSM}	$t_p = 10 \text{ ms, sin } 180^{\circ}$	°, T _j = 150 °C	900	Α
Tj			-40 175	°C
Module				
I _{t(RMS)}	T _{terminal} = 80 °C, 20	A per spring	160	Α
T _{stg}	module without TIM	1	-40 125	°C
V _{isol}	AC sinus 50 Hz, t =	1 min	2500	V

Characteristics									
Symbol	Conditions		min.	typ.	max.	Unit			
Inverter - IGBT									
V _{CE(sat)}	I _C = 150 A	T _j = 25 °C		1.85	2.10	V			
l l	V _{GE} = 15 V chiplevel	T _j = 150 °C		2.25	2.45	V			
V_{CE0}	chiplevel	T _j = 25 °C		0.80	0.90	V			
	Criipievei	T _j = 150 °C		0.70	0.80	V			
r _{CE}	V _{GE} = 15 V	T _j = 25 °C		7.0	8.0	mΩ			
	chiplevel	T _j = 150 °C		10	11	mΩ			
$V_{\text{GE(th)}}$	$V_{GE} = V_{CE}$, $I_C = 6 \text{ m}$	A	5	5.8	6.5	V			
I _{CES}	$V_{GE} = 0 \text{ V}, V_{CE} = 12$	00 V, T _j = 25 °C			1.5	mA			
C _{ies}	V 05.V	f = 1 MHz		8.80		nF			
Coes	$V_{CE} = 25 \text{ V}$ $V_{GF} = 0 \text{ V}$	f = 1 MHz		0.58		nF			
C _{res}	VGE - O V	f = 1 MHz		0.47		nF			
Q_G	V _{GE} = - 8 V+ 15 V			850		nC			
R _{Gint}	T _j = 25 °C			5.0		Ω			
t _{d(on)}	$V_{CC} = 600 \text{ V}$	T _j = 150 °C		165		ns			
t _r	I _C = 150 A	T _j = 150 °C		50		ns			
E _{on}	$R_{G \text{ on}} = 1 \Omega$ $R_{G \text{ off}} = 1 \Omega$	T _j = 150 °C		22.5		mJ			
t _{d(off)}	di/dt _{on} = 2840 A/μs	T _j = 150 °C		390		ns			
t _f	di/dt _{off} = 1880 A/μs			80		ns			
E _{off}	V _{GE} = +15/-15 V	T _j = 150 °C		14		mJ			
R _{th(j-s)}	per IGBT, λ _{paste} =0.8		0.26		K/W				
R _{th(j-s)}	per IGBT, λ _{paste} =2.5		0.16		K/W				



MiniSKiiP® 3

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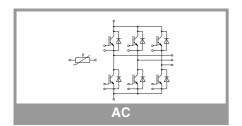
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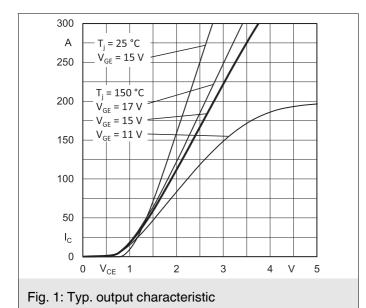
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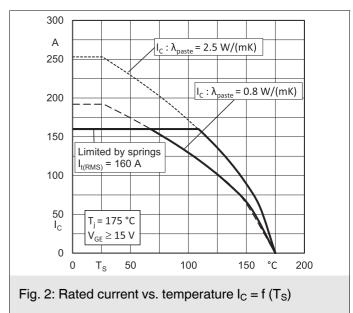
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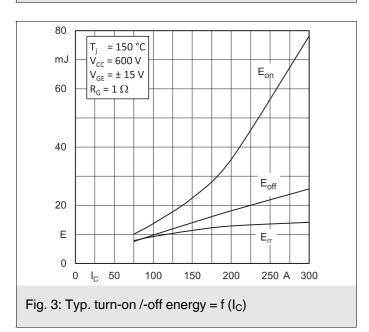
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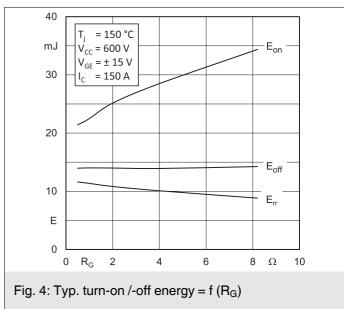
Characte	eristics					
Symbol	Conditions		min.	typ.	max.	Unit
Inverse -	Diode	·				•
$V_F = V_{EC}$	I _F = 150 A	T _j = 25 °C		2.14	2.46	V
	V _{GE} = 0 V chiplevel	T _j = 150 °C		2.07	2.38	V
V_{F0}	chiplevel	T _j = 25 °C		1.30	1.50	V
	Chipievei	T _j = 150 °C		0.90	1.10	V
r _F	chiplevel	T _j = 25 °C		5.6	6.4	mΩ
	Chipievei	T _j = 150 °C		7.8	8.5	mΩ
I _{RRM}	I _F = 150 A	T _j = 150 °C		188		Α
Q _{rr}	di/dt _{off} = 4020 A/ μ s V _{GE} = +15/-15 V	T _j = 150 °C		27		μC
E _{rr}	$V_{CC} = 600 \text{ V}$	T _j = 150 °C		11.4		mJ
R _{th(j-s)}	per Diode, $\lambda_{paste}=0$.	8 W/(mK)		0.45		K/W
R _{th(j-s)}	per Diode, λ _{paste} =2.	5 W/(mK)		0.24		K/W
Module						
L _{CE}				-		nΗ
Ms	to heat sink	2		2.5	Nm	
W				82		g
Temperat	ture Sensor					
R ₁₀₀	T _r =100°C (R ₂₅ =100		1670 ± 3%		Ω	
R _(T)	$R_{(T)}=1000\Omega[1+A(T-25^{\circ}C)+B(T-25^{\circ}C)^{2}]$, A = 7.635*10 ^{-3°} C ⁻¹ , B = 1.731*10 ^{-5°} C ⁻²					

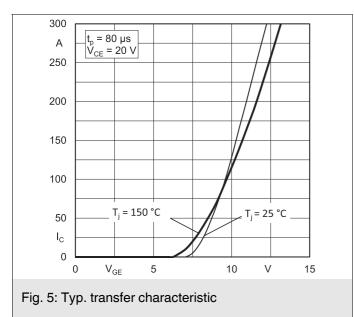


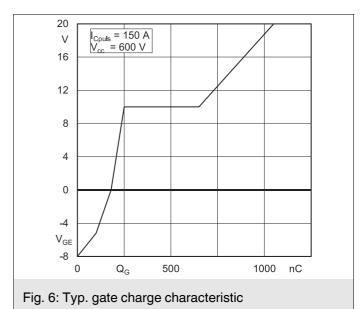












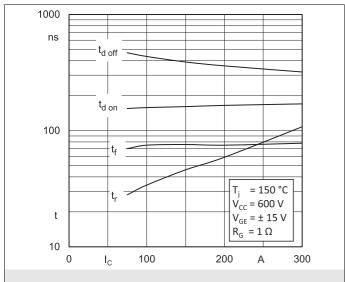


Fig. 7: Typ. switching times vs. I_C

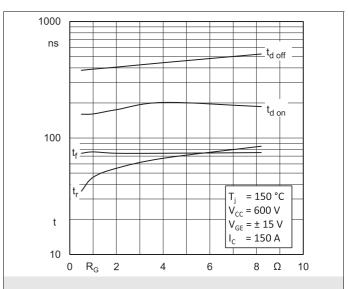


Fig. 8: Typ. switching times vs. gate resistor R_{G}

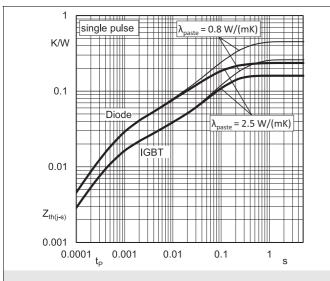


Fig. 9: Typ. transient thermal impedance

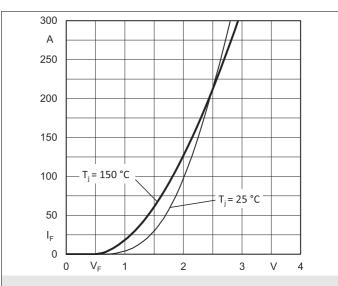


Fig. 10: Typ. CAL diode forward characteristic

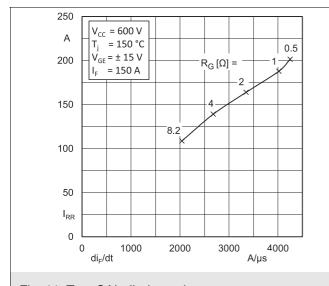


Fig. 11: Typ. CAL diode peak reverse recovery current

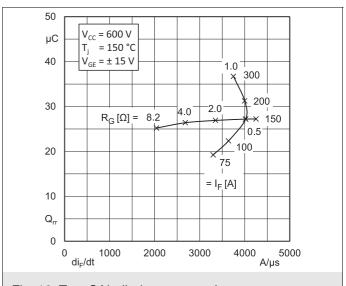
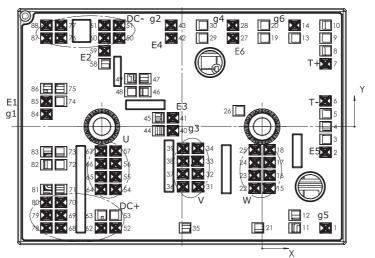


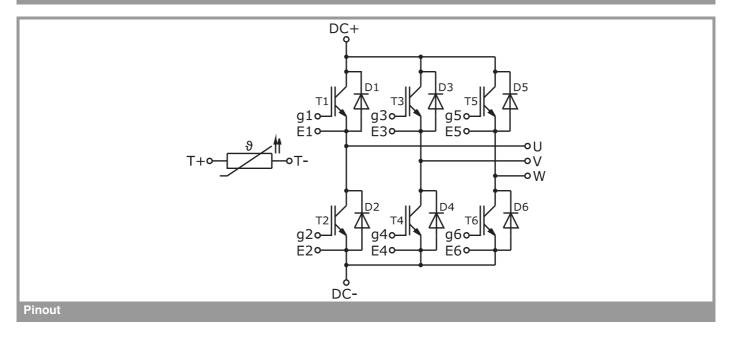
Fig. 12: Typ. CAL diode recovery charge

Pin out											
Pin	X	Υ	Function	Pin	Χ	Υ	Function	Pin	Χ	Υ	Function
1	15,83	-25,30	g5	31	-16,05	-15,02	٧	61	-39,33	25,30	DC-
2	15,83	-6,40	E5	32	-16,05	-11,82	٧	62	-40,23	-25,30	DC+
3	15,83	-3,20		33	-16,05	-8,62	٧	63	-40,23	-22,10	
4	15,83	0		34	-16,05	-5,42	٧	64	-40,23	-15,70	U
5	15,83	3,20		35	-19,23	-25,30		65	-40,23	-12,50	U
6	15,83	6,40	T-	36	-19,70	-15,02	٧	66	-40,23	-9,30	U
7	15,83	15,70	T+	37	-19,70	-11,82		67	-40,23	-6,10	U
8	15,83	18,90		38	-19,70	-8,62	٧	68	-50,18	-25,30	DC+
9	15,83	22,10		39	-19,70		٧	69	-50,18	-22,10	
10	15,83	25,30		40	-22,26	-1,00	g3	70	-50,18	-18,90	DC+
11	8,13	-25,30		41	-22,26	2,20	E3	71	-50,18	-15,70	
12	8,13	-22,10		42	-22,68		E4	72	-50,18		
13	8,13			43	-22,68			73	-50,18		
14	8,13	25,30	g6	44	-25,91	-1,00		74	-50,18	6,30	
15	1,83	-15,39	W	45	-25,91	2,20		75	-50,18		
16	1,83	-12,19	W	46	-29,18			76	-50,18		DC-
17	1,83	-8,99	W	47	-29,18			77	-50,18	25,30	DC-
18	1,83	-5,79	W	48	-32,83	8,74		78	-53,83	-25,30	DC+
19	0,43	22,10		49	-32,83	11,94		79	-53,83	-22,10	DC+
20	0,43	25,30		50	-35,68	22,10		80	-53,83	-18,90	
21	-1,08			51	-35,68			81	-53,83		
22	-1,83		W	52	-36,58			82	-53,83		
23	-1,83	-12,19	W	53	-36,58	-22,10		83	-53,83		
24	-1,83	-8,99	W	54	-36,58		U	84	-53,83	3,10	g1
25	-1,83	-5,79	W	55	-36,58			85	-53,83	6,30	
26	-5,83	3,95		56	-36,58			86	-53,83	9,50	
27	-7,28	22,10	E6	57	-36,58			87	-53,83		
28	-7,28	25,30	g4	58	-39,33	15,70		88	-53,83	25,30	DC-
29	-14,98	22,10		59	-39,33	18,90	E2				
30	-14,98	25,30		60	-39,33	22,10	DC-				

all values in mm



Pinout and Dimensions



This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

*IMPORTANT INFORMATION AND WARNINGS

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